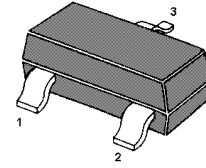


NPN Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

The transistor is subdivided into two groups C and D according to its DC current gain.



1.BASE 2.EMITTER 3.COLLECTOR
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	25	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	2	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 1\text{ V}$, $I_C = 5\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 100\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 1.5\text{ A}$	h_{FE}	45	-	-
	h_{FE}	100	250	-
	h_{FE}	160	300	-
	h_{FE}	40	-	-
Collector Base Cutoff Current at $V_{CB} = 35\text{ V}$	I_{CBO}	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 6\text{ V}$	I_{EBO}	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at $I_C = 2\text{ mA}$	$V_{(BR)CEO}$	25	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $I_C = 1.5\text{ A}$, $I_B = 100\text{ mA}$	$V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $I_C = 1.5\text{ A}$, $I_B = 100\text{ mA}$	$V_{BE(sat)}$	-	1.2	V
Base Emitter Voltage at $V_{CE} = 1\text{ V}$, $I_C = 10\text{ mA}$	$V_{BE(on)}$	-	1	V
Transition Frequency at $V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$	f_T	100	-	MHz